

# Martin Albrecht

## List of Publications by Year in descending order

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276  
papers

10,183  
citations

39113

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286  
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286  
docs citations

286  
times ranked

9776  
citing authors

#	ARTICLE	IF	CITATIONS
1	A consistent picture of excitations in cubic BaSnO <sub>3</sub> revealed by combining theory and experiment. Communications Materials, 2022, 3, .	2.9	10
2	Molecular beam epitaxy of single-crystalline bixbyite $\text{O}_{1-x}\text{Ga}_2\text{O}_3$ . Physical Review Materials, 2022, 6, .	0.9	5
3	Toward Precise n-Type Doping Control in MOVPE-Grown $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> Thin Films by Deep-Learning Approach. Crystals, 2022, 12, 8.	1.0	7
4	Machine learning supported analysis of MOVPE grown $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> thin films on sapphire. Journal of Crystal Growth, 2022, 592, 126737.	0.7	7
5	Formation of voids and their role in the recovery of sputtered AlN during high-temperature annealing. Journal of Applied Physics, 2022, 131, .	1.1	5
6	Bulk single crystals of $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> and Ga-based spinels as ultra-wide bandgap transparent semiconducting oxides. Progress in Crystal Growth and Characterization of Materials, 2021, 67, 100511.	1.8	47
7	Role of Metal Vacancies in the Mechanism of Thermal Degradation of InGaN Quantum Wells. ACS Applied Materials & Interfaces, 2021, 13, 7476-7484.	4.0	15
8	Fingerprints of optical absorption in the perovskite LaInO <sub>3</sub> : Insight from many-body theory and experiment. Physical Review B, 2021, 103, .	1.1	6
9	Influence of Sr deficiency on structural and electrical properties of SrTiO <sub>3</sub> thin films grown by metal-organic vapor phase epitaxy. Scientific Reports, 2021, 11, 7497.	1.6	10
10	Melt Growth and Physical Properties of Bulk LaInO <sub>3</sub> Single Crystals. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100016.	0.8	9
11	Epitaxial BaSnO <sub>3</sub> thin films with low dislocation density grown on lattice matched LaInO <sub>3</sub> substrates. Nanotechnology, 2021, 32, 505609.	1.3	1
12	Impact of chamber pressure and Si-doping on the surface morphology and electrical properties of homoepitaxial (100) $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> thin films grown by MOVPE. Journal Physics D: Applied Physics, 2021, 54, 034003.	1.3	26
13	Role of oxygen diffusion in the dislocation reduction of epitaxial AlN on sapphire during high-temperature annealing. Journal of Applied Physics, 2021, 130, .	1.1	12
14	Fast homoepitaxial growth of (100) $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> thin films via MOVPE. AIP Advances, 2021, 11, .	0.6	22
15	Comment on "Phase transformation in MOCVD growth of (Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> thin films" [APL Mater. 8, 031104 (2020)]. APL Materials, 2020, 8, 089101.	2.2	5
16	Single-photon emission from isolated monolayer islands of InGaN. Light: Science and Applications, 2020, 9, 159.	7.7	20
17	Step flow growth of $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> thin films on vicinal (100) $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> substrates grown by MOVPE. Applied Physics Letters, 2020, 116, .	1.5	59
18	Approaching the high intrinsic electrical resistivity of NbO <sub>2</sub> in epitaxially grown films. Applied Physics Letters, 2020, 116, 182103.	1.5	14

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19	Plasma-assisted molecular beam epitaxy of NiO on GaN(00.1). Journal of Applied Physics, 2020, 127, .	1.1	15
20	Substrate-orientation dependence of $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> (100), (010), (001), and (2 $\hat{A}$ 01) homoepitaxy by indium-mediated metal-exchange catalyzed molecular beam epitaxy (MEXCAT-MBE). APL Materials, 2020, 8, .	2.2	80
21	Controlling the relaxation mechanism of low strain Si $\hat{A}$ <sup>+</sup> <i>x</i> <i>Ge</i> <i>x</i> <i>/Si</i> (001) layers and reducing the threading dislocation density by providing a preexisting dislocation source. Journal of Applied Physics, 2020, 128, .	1.1	6
22	Control of phase formation of (Al <i>x</i> Ga $\hat{A}$ <sup>+</sup> <i>x</i> ) <sub>2</sub> O <sub>3</sub> thin films on c-plane Al <sub>2</sub> O <sub>3</sub> . Journal Physics D: Applied Physics, 2020, 53, 485105.	1.3	24
23	Influence of strain on the indium incorporation in (0001) GaN. Physical Review Materials, 2020, 4, .	0.9	9
24	Role of the interface in controlling the epitaxial relationship between orthorhombic $\text{LaInO}_3$ and cubic $\text{BaSnO}_3$ . Physical Review Materials, 2020, 4, .	0.9	9
25	Investigating the ranges of (meta)stable phase formation in $\text{O}_3$ . Physical Review Materials, 2020, 4, .	0.9	12
26	Kinetic Monte Carlo model for homoepitaxial growth of $\text{Ga}_2\text{O}_3$ . Physical Review Research, 2020, 2, .	1.3	10
27	Improved performance of UVC-LEDs by combination of high-temperature annealing and epitaxially laterally overgrown AlN/sapphire. Photonics Research, 2020, 8, 589.	3.4	49
28	High-temperature annealing of AlN films grown on 4H-SiC. AIP Advances, 2020, 10, .	0.6	8
29	Impact of the substrate lattice constant on the emission properties of InGa <sub>n</sub> /Ga <sub>n</sub> short-period superlattices grown by plasma assisted MBE. Superlattices and Microstructures, 2019, 133, 106209.	1.4	8
30	Unusual Polarization Dependence of Dislocation-Related Luminescence in n-GaN. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900305.	0.8	3
31	Asymmetry of the Atomic Core Structure of Dissociated $\hat{A}$ -Screw Dislocation in GaN Probed by Polarization Optical Spectroscopy. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900169.	1.2	2
32	Role of hole confinement in the recombination properties of InGa <sub>n</sub> quantum structures. Scientific Reports, 2019, 9, 9047.	1.6	6
33	Indium incorporation in homoepitaxial $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> thin films grown by metal organic vapor phase epitaxy. Journal of Applied Physics, 2019, 125, .	1.1	14
34	Stabilization of sputtered AlN/sapphire templates during high temperature annealing. Journal of Crystal Growth, 2019, 512, 142-146.	0.7	40
35	Influence of 2s Bloch wave state excitations on quantitative HAADF STEM imaging. Physical Review B, 2019, 100, .	1.1	1
36	Interface polarization model for a 2-dimensional electron gas at the BaSnO <sub>3</sub> /LaInO <sub>3</sub> interface. Scientific Reports, 2019, 9, 16202.	1.6	19

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37	Step-flow growth in homoepitaxy of $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> (100) – The influence of the miscut direction and faceting. APL Materials, 2019, 7, .	2.2	73
38	Faceting and metal-exchange catalysis in (010) $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> thin films homoepitaxially grown by plasma-assisted molecular beam epitaxy. APL Materials, 2019, 7, .	2.2	53
39	Ultra-wide bandgap, conductive, high mobility, and high quality melt-grown bulk ZnGa <sub>2</sub> O <sub>4</sub> single crystals. APL Materials, 2019, 7, .	2.2	74
40	Doping of Czochralski-grown bulk $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> single crystals with Cr, Ce and Al. Journal of Crystal Growth, 2018, 486, 82-90.	0.7	83
41	MOVPE Growth of Smooth and Homogeneous Al <sub>0.8</sub> Ga <sub>0.2</sub> N:Si Superlattices as UVC Laser Cladding Layers. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800005.	0.8	7
42	Heteroepitaxial Growth of T-Nb <sub>2</sub> O <sub>5</sub> on SrTiO <sub>3</sub> . Nanomaterials, 2018, 8, 895.	1.9	8
43	Defect generation by nitrogen during pulsed sputter deposition of GaN. Journal of Applied Physics, 2018, 124, 175701.	1.1	6
44	Intentional polarity conversion of AlN epitaxial layers by oxygen. Scientific Reports, 2018, 8, 14111.	1.6	36
45	Peculiarities of plastic relaxation of (0001) InGa <sub>N</sub> epilayers and their consequences for pseudo-substrate application. Applied Physics Letters, 2018, 113, .	1.5	17
46	A predictive model for plastic relaxation in (0001)-oriented wurtzite thin films and heterostructures. Journal of Applied Physics, 2018, 124, .	1.1	8
47	Dependence of indium content in monolayer-thick InGa <sub>N</sub> quantum wells on growth temperature in In <sub>x</sub> Ga <sub>1-x</sub> N/In <sub>0.02</sub> Ga <sub>0.98</sub> N superlattices. Journal of Applied Physics, 2018, 124, 065701.	1.1	10
48	Elastically frustrated rehybridization: Origin of chemical order and compositional limits in InGa <sub>N</sub> quantum wells. Physical Review Materials, 2018, 2, .	0.9	36
49	Editors' Choice – Si- and Sn-Doped Homoepitaxial $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> Layers Grown by MOVPE on (010)-Oriented Substrates. ECS Journal of Solid State Science and Technology, 2017, 6, Q3040-Q3044.	0.9	219
50	Exciton emission of quasi-2D InGa <sub>N</sub> in GaN matrix grown by molecular beam epitaxy. Scientific Reports, 2017, 7, 46420.	1.6	14
51	In/GaN(0001)-(3 $\bar{A}$ -3)R30 $\hat{A}$ adsorbate structure as a template for embedded (In, Ga)N/GaN monolayers and short-period superlattices. Applied Physics Letters, 2017, 110, .	1.5	21
52	Melt growth and properties of bulk BaSnO <sub>3</sub> single crystals. Journal of Physics Condensed Matter, 2017, 29, 075701.	0.7	28
53	Influence of incoherent twin boundaries on the electrical properties of $\text{In}^{2+}$ -Ga <sub>2</sub> O <sub>3</sub> layers homoepitaxially grown by metal-organic vapor phase epitaxy. Journal of Applied Physics, 2017, 122, .	1.1	69
54	Impact of sapphire nitridation on formation of Al-polar inversion domains in N-polar AlN epitaxial layers. Journal of Applied Physics, 2017, 122, .	1.1	28

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55	Evolution of planar defects during homoepitaxial growth of $\text{In}^2\text{-Ga}_2\text{O}_3$ layers on (100) substrates – A quantitative model. Journal of Applied Physics, 2016, 120, .	1.1	75
56	Investigation of interface abruptness and In content in (In,Ga)N/GaN superlattices. Journal of Applied Physics, 2016, 120, 125307.	1.1	14
57	Stacking fault domains as sources of a-type threading dislocations in III-nitride heterostructures. Applied Physics Letters, 2016, 108, .	1.5	16
58	Polarization-induced confinement of continuous hole-states in highly pumped, industrial-grade, green InGaN quantum wells. Journal of Applied Physics, 2016, 119, 215707.	1.1	5
59	Diffusion of oxygen in bulk GaN crystals at high temperature and at high pressure. Journal of Crystal Growth, 2016, 449, 35-42.	0.7	8
60	Origin of brown coloration in top-seeded solution grown $\text{SrTiO}_3$ crystals. CrystEngComm, 2016, 18, 4580-4586.	1.3	4
61	Comparison of the Luminous Efficiencies of Ga- and N-Polar $\text{In}_x\text{Ga}_{1-x}\text{N}$ LEDs. Physical Review Applied, 2016, 6, .	1.5	16
62	Evolution of impurity incorporation during ammonothermal growth of GaN. Journal of Crystal Growth, 2016, 456, 51-57.	0.7	13
63	Free-standing millimetre-long $\text{Bi}_2\text{Te}_3$ sub-micron belts catalyzed by $\text{TiO}_2$ nanoparticles. Nanoscale Research Letters, 2016, 11, 308.	3.1	3
64	Atomic signatures of local environment from core-level spectroscopy in $\text{In}^2\text{-Ga}_2\text{O}_3$ . Physical Review B, 2016, 94, .	1.1	28
65	High-Output Power Ultraviolet Light Source from Quasi-2D GaN Quantum Structure. Advanced Materials, 2016, 28, 7978-7983.	11.1	72
66	Polarity Control in Group-III Nitrides beyond Pragmatism. Physical Review Applied, 2016, 5, .	1.5	94
67	Semiconducting Sn-doped $\text{In}^2\text{-Ga}_2\text{O}_3$ homoepitaxial layers grown by metal organic vapour-phase epitaxy. Journal of Materials Science, 2016, 51, 3650-3656.	1.7	116
68	Analysis of the exciton-LO-phonon coupling in single wurtzite GaN quantum dots. Physical Review B, 2015, 92, .	1.1	20
69	Electrical compensation by Ga vacancies in $\text{Ga}_2\text{O}_3$ thin films. Applied Physics Letters, 2015, 106, .	1.5	142
70	Effect of indium as a surfactant in $\text{In}_x\text{Ga}_{1-x}\text{N}$ epitaxial growth on $\text{In}^2\text{-Ga}_2\text{O}_3$ by metal organic vapour phase epitaxy. Semiconductor Science and Technology, 2015, 30, 024013.	1.0	40
71	$\text{MgGa}_2\text{O}_4$ as a new wide bandgap transparent semiconducting oxide: growth and properties of bulk single crystals. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1455-1460.	0.8	56
72	Kinetic analysis of the reduction of 4-nitrophenol catalyzed by Au/Pd nanoalloys immobilized in spherical polyelectrolyte brushes. Physical Chemistry Chemical Physics, 2015, 17, 28137-28143.	1.3	83

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73	Temperature-dependent thermoelectric properties of individual silver nanowires. <i>Physical Review B</i> , 2015, 91, .	1.1	69
74	Epitaxial stabilization of pseudomorphic $\text{In}_2\text{Ga}_2\text{O}_3$ on sapphire (0001). <i>Applied Physics Express</i> , 2015, 8, 011101.	1.1	104
75	Manipulation of In(Ga)N monolayer epitaxy by MBE. , 2015, , .		0
76	Semipolar ( $202\text{\AA}^{-1}$ ) GaN laser diodes operating at $388\text{\AA}$ nm grown by plasma-assisted molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014, 32, 02C115.	0.6	1
77	Recombination dynamics in In <sub>x</sub> Ga <sub>1-x</sub> N quantum wells—Contribution of excited subband recombination to carrier leakage. <i>Applied Physics Letters</i> , 2014, 105, 181109.	1.5	9
78	The discrepancies between theory and experiment in the optical emission of monolayer In(Ga)N quantum wells revisited by transmission electron microscopy. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	48
79	Origin of the unusually strong luminescence of $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"> \langle \text{mml:mi>a</mml:mi> \langle \text{mml:math}> \text{-type screw dislocations in GaN. } \text{Physical Review B}$ , 2014, 90, .	1.1	19
80	Coloration and oxygen vacancies in wide band gap oxide semiconductors: Absorption at metallic nanoparticles induced by vacancy clustering—A case study on indium oxide. <i>Journal of Applied Physics</i> , 2014, 115, 053504.	1.1	27
81	Homoepitaxial growth of $\text{In}_2\text{Ga}_2\text{O}_3$ layers by metal-organic vapor phase epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 27-33.	0.8	170
82	Three dimensional analysis of the composition in solid alloys by variable probe in scanning transmission electron microscopy. <i>Ultramicroscopy</i> , 2014, 146, 62-70.	0.8	8
83	On the nature and temperature dependence of the fundamental band gap of $\text{In}_2\text{Ga}_2\text{O}_3$ . <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 54-58.	0.8	96
84	Growth, characterization, and properties of bulk $\text{SnO}_2$ single crystals. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 66-73.	0.8	46
85	Separating strain from composition in unit cell parameter maps obtained from aberration corrected high resolution transmission electron microscopy imaging. <i>Journal of Applied Physics</i> , 2014, 115, 033113.	1.1	10
86	Temperature-dependent electrical characterization of exfoliated $\text{In}_2\text{Ga}_2\text{O}_3$ micro flakes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 543-549.	0.8	25
87	High-voltage field effect transistors with wide-bandgap $\text{In}_2\text{Ga}_2\text{O}_3$ nanomembranes. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	288
88	Structural properties of Si-doped $\text{In}_2\text{Ga}_2\text{O}_3$ layers grown by MOVPE. <i>Journal of Crystal Growth</i> , 2014, 401, 665-669.	0.7	133
89	Methods for Scanning Transmission Electron Microscopy High Angle Annular Dark Field Based for Three Dimensional Analysis of the Local Composition in Solid Alloys. <i>Microscopy and Microanalysis</i> , 2014, 20, 594-595.	0.2	0
90	The structure of AuPd nanoalloys anchored on spherical polyelectrolyte brushes determined by X-ray absorption spectroscopy. <i>Faraday Discussions</i> , 2013, 162, 45.	1.6	12



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109	Catalytic Activity of Faceted Gold Nanoparticles Studied by a Model Reaction: Evidence for Substrate-Induced Surface Restructuring. <i>ACS Catalysis</i> , 2011, 1, 908-916.	5.5	504
110	Ultraviolet luminescence in AlN. <i>Physica Status Solidi (B): Basic Research</i> , 2011, 248, 1513-1518.	0.7	49
111	A new approach to grow $\text{C}\delta$ -doped GaN thick epitaxial layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 2120-2122.	0.8	10
112	The use of heater-magnet module for Czochralski growth of PV silicon crystals with quadratic cross section. <i>Journal of Crystal Growth</i> , 2011, 318, 249-254.	0.7	25
113	Pyramidal inversion domain boundaries revisited. <i>Applied Physics Letters</i> , 2011, 99, .	1.5	21
114	Mismatch relaxation by stacking fault formation of AlN islands in AlGaIn/GaN structures on m-plane GaN substrates. <i>Applied Physics Letters</i> , 2011, 99, 061901.	1.5	13
115	Spatially Resolved Thermoluminescence in a Scanning Electron Microscope. <i>Advances in Imaging and Electron Physics</i> , 2011, , 337-359.	0.1	2
116	Coloration of Wide-Bandgap Semiconductors Originating from Particle Plasmons. , 2010, , .		0
117	Growth of intersubband GaN/AlGaIn heterostructures. <i>Proceedings of SPIE</i> , 2010, , .	0.8	5
118	Czochralski growth and characterization of $\text{In}_{0.2}\text{Ga}_{0.8}\text{O}_{0.3}$ single crystals. <i>Crystal Research and Technology</i> , 2010, 45, 1229-1236.	0.6	378
119	Structure and luminescence of sol-gel synthesized anatase nanoparticles. <i>Journal of Physics: Conference Series</i> , 2010, 209, 012039.	0.3	11
120	Microscopic lateral overgrowth by physical vapour transport of GaN on self-organized diamond-like carbon masks. <i>Crystal Research and Technology</i> , 2009, 44, 1078-1082.	0.6	2
121	Self-assembled and ordered growth of silicon and germanium nanowires. <i>Superlattices and Microstructures</i> , 2009, 46, 277-285.	1.4	23
122	Nitride-based quantum structures and devices on modified GaN substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009, 206, 1130-1134.	0.8	17
123	The role of carbon in transport processes during PVT growth of bulk GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, 1484-1487.	0.8	8
124	Coloration of zinc oxide crystals originating from particle plasmons. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, 2658-2660.	0.8	7
125	Boron- and stoichiometry-related defect engineering during $\text{B}_{0.2}\text{O}_{0.3}$ -free GaAs crystal growth. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, 2778-2784.	0.8	3
126	State of Transition Metal Catalysts During Carbon Nanotube Growth. <i>Journal of Physical Chemistry C</i> , 2009, 113, 1648-1656.	1.5	166

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127	Bi-stable behaviour in GaN-based resonant tunnelling diode structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 431-434.	0.8	17
128	Influence of substrate misorientation on properties of InGaN layers grown on freestanding GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 1485-1487.	0.8	12
129	Electro-optical intersubband modulators at telecommunication wavelengths based on GaN/AlN quantum wells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 1093-1095.	0.8	1
130	Surface preparation of AlN substrates. <i>Crystal Research and Technology</i> , 2008, 43, 651-655.	0.6	12
131	Defect distribution in boron-reduced GaAs crystals grown by vapour-pressure-controlled Czochralski technique. <i>Journal of Crystal Growth</i> , 2008, 310, 1418-1423.	0.7	9
132	Homoepitaxial seeding and growth of bulk AlN by sublimation. <i>Journal of Crystal Growth</i> , 2008, 310, 930-934.	0.7	35
133	Properties of rare-earth scandate single crystals (Re=Nd <sup>2+</sup> Dy). <i>Journal of Crystal Growth</i> , 2008, 310, 2649-2658.	0.7	137
134	Energetic and kinetic aspects of the growth of pseudomorphic SiGe islands. <i>Journal of Crystal Growth</i> , 2008, 310, 3261-3267.	0.7	1
135	Burgers vector analysis by three-dimensional laser-scattering tomography. <i>Journal of Crystal Growth</i> , 2008, 310, 4031-4034.	0.7	2
136	GaN/AlN short-period superlattices for intersubband optoelectronics: A systematic study of their epitaxial growth, design, and performance. <i>Journal of Applied Physics</i> , 2008, 104, 093501.	1.1	165
137	Light Confinement at Ultrasharp Metallic Tips. <i>Japanese Journal of Applied Physics</i> , 2008, 47, 6051.	0.8	21
138	Thermoluminescence in a scanning electron microscope. <i>Journal of Applied Physics</i> , 2008, 104, 083710.	1.1	1
139	Nonradiative recombination at threading dislocations in n-type GaN: Studied by cathodoluminescence and defect selective etching. <i>Applied Physics Letters</i> , 2008, 92, .	1.5	74
140	TEM study of quaternary InGaAsN/GaAs quantum well structures grown by molecular beam epitaxy. , 2008, , 83-84.		0
141	Strain-induced interface instability in GaN/AlN multiple quantum wells. <i>Applied Physics Letters</i> , 2007, 91, 061927.	1.5	37
142	Compositional Correlation and Anticorrelation in Quaternary Alloys: Competition Between Bulk Thermodynamics and Surface Kinetics. <i>Physical Review Letters</i> , 2007, 99, 206103.	2.9	16
143	Screening the built-in electric field in 4H silicon carbide stacking faults. <i>Applied Physics Letters</i> , 2007, 90, 111902.	1.5	9
144	Short-wavelength intersubband electroabsorption modulation based on electron tunneling between GaN/AlN coupled quantum wells. <i>Applied Physics Letters</i> , 2007, 90, 223511.	1.5	54

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145	Correlation between luminescence and compositional striations in InGaN layers grown on miscut GaN substrates. Applied Physics Letters, 2007, 91, .	1.5	37
146	On the Origin of the Unexpected Annealing Behavior of GaInNAs Quantum Wells. Japanese Journal of Applied Physics, 2007, 46, L614-L616.	0.8	0
147	Grating-Coupling of Surface Plasmons onto Metallic Tips: A Nanoconfined Light Source. Nano Letters, 2007, 7, 2784-2788.	4.5	468
148	Cathodoluminescence spectroscopy of epitaxial-lateral-overgrown nonpolar (11-20) and semipolar (11-22) GaN in relation to microstructural characterization. Journal of Applied Physics, 2007, 101, 113101.	1.1	99
149	Compensating defects in Si-doped AlN bulk crystals. Physica B: Condensed Matter, 2007, 401-402, 323-326.	1.3	19
150	Photoluminescence, cathodo-luminescence and micro-Raman spectroscopy of as-grown stacking faults in 4H-SiC. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 1513-1516.	0.8	0
151	Investigations of the growth conditions for GaN-bulk crystals grown by the sublimation technique. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2219-2222.	0.8	3
152	Cathodoluminescence investigation of stacking faults extension in 4H-SiC. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 2222-2228.	0.8	5
153	n-type conductivity in sublimation-grown AlN bulk crystals. Physica Status Solidi - Rapid Research Letters, 2007, 1, 147-149.	1.2	15
154	Electron confinement in strongly coupled GaN/AlN quantum wells. Applied Physics Letters, 2006, 88, 153113.	1.5	48
155	Systematic experimental and theoretical investigation of intersubband absorption in GaN/AlN quantum wells. Physical Review B, 2006, 73, .	1.1	239
156	Growth and characterization of AlInN/GaN quantum wells for high-speed intersubband devices at telecommunication wavelengths. , 2006, , .		5
157	Effect of growth temperature on AlGaInN layers: a TEM analysis. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1400-1403.	0.8	0
158	Preparation and characterisation of tantalum carbide as an optional crucible material for bulk aluminium nitride crystal growth via physical vapour transport. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1608-1612.	0.8	14
159	Si-doped GaN/AlN quantum dot superlattices for optoelectronics at telecommunication wavelengths. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1754-1758.	0.8	3
160	Optical and theoretical study of strong electron coupling in double GaN/AlN quantum wells. Physica Status Solidi (B): Basic Research, 2006, 243, 1630-1633.	0.7	8
161	Cathodoluminescence in transmission electron microscopy. Journal of Microscopy, 2006, 224, 79-85.	0.8	20
162	Formation and properties of stacking faults in nitrogen-doped 4H-SiC. Physica B: Condensed Matter, 2006, 376-377, 338-341.	1.3	31

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164	MBE growth of nitride-based photovoltaic intersubband detectors. <i>Superlattices and Microstructures</i> , 2006, 40, 418-425.	1.4	7
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